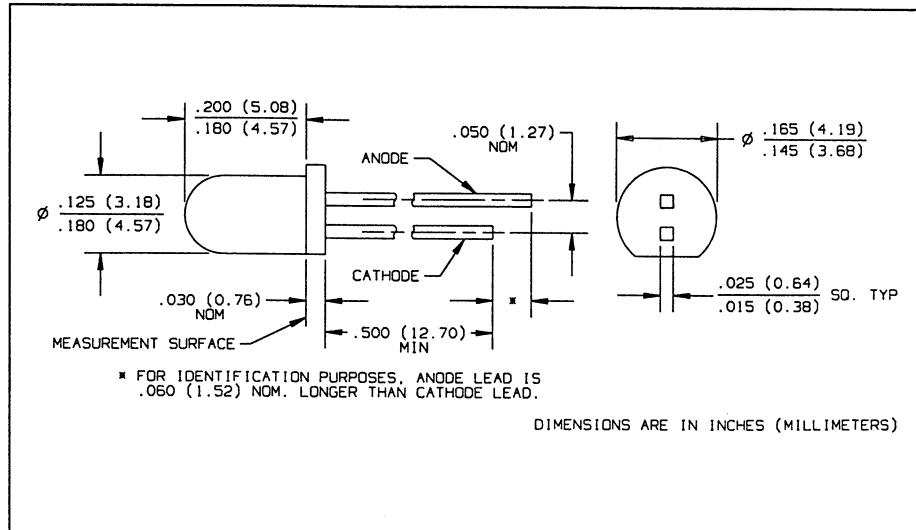
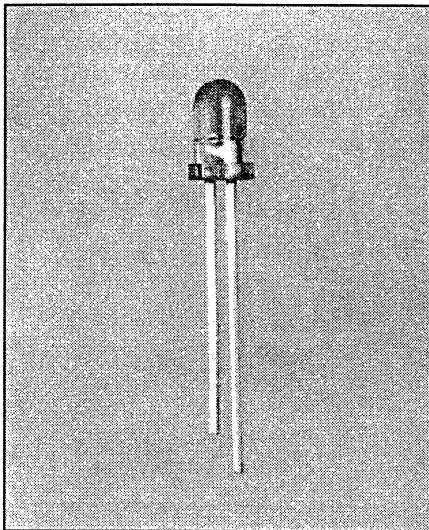


GaAlAs Plastic Infrared Emitting Diodes

Types OP265A, OP265B, OP265C, OP265D



Features

- Narrow irradiance pattern
- Mechanically and spectrally matched to the OP505, OP535 series devices
- Significantly higher power output than GaAs at equivalent drive currents
- Wavelength matched to silicon's peak response
- T-1 package style

Description

The OP265 series devices are 890nm high intensity gallium aluminum arsenide infrared emitting diodes molded in IR transmissive amber tinted epoxy packages. The narrow irradiance pattern provides high on-axis intensity for excellent coupling efficiency.

Replaces

K6600

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

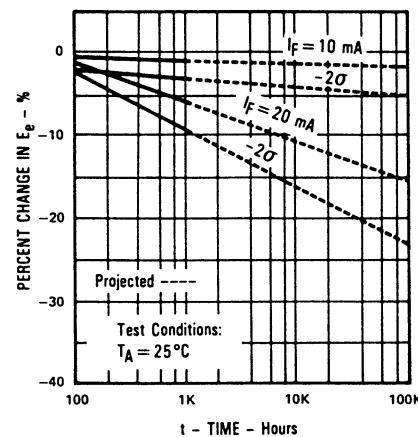
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μ s pulse width, 300 pps)	3.0 A
Storage and Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	260° C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

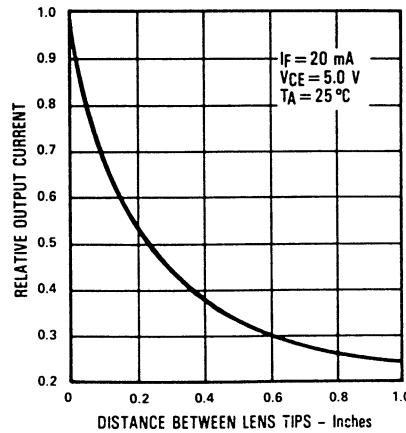
- RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. A max. of 20 grams force may be applied to the leads when soldering.
- Derate linearly 1.33 mW/ $^\circ C$ above 25° C.
- $E_e(APT)$ is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99 mm) from the measurement surface. $E_e(APT)$ is not necessarily uniform within the measured area.

Typical Performance Curves

Percent Changes in Radiant Intensity
vs Time



Coupling Characteristics
of OP265 and OP505



Types OP265A, OP265B, OP265C, OP265D

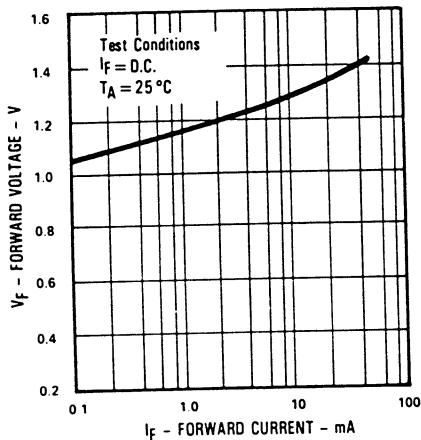
Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

SYMBOL	PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITIONS
$E_e(APT)$	Apertured Radiant Incidence	OP265D OP265C OP265B OP265A	0.54 0.54 1.65 2.70		3.30 4.70	mW/cm^2	$I_F = 20 mA^{(3)}$ $I_F = 20 mA^{(3)}$ $I_F = 20 mA^{(3)}$ $I_F = 20 mA^{(3)}$ $I_F = 20 mA^{(3)}$
V_F	Forward Voltage				1.80	V	$I_F = 20 mA$
I_R	Reverse Current				100	μA	$V_R = 2 V$
λ_p	Wavelength at Peak Emission				890	nm	$I_F = 10 mA$
B	Spectral Bandwidth Between Half Power Points				80	nm	$I_F = 10 mA$
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature				+0.18	$nm/^\circ C$	$I_F = \text{Constant}$
θ_{HP}	Emission Angle at Half Power Points				18	Deg.	$I_F = 20 mA$
t_r	Output Rise Time				500	ns	$I_F(PK) = 100 mA,$ $PW = 10 \mu s, D.C. = 10\%$
t_f	Output Fall Time				250	ns	

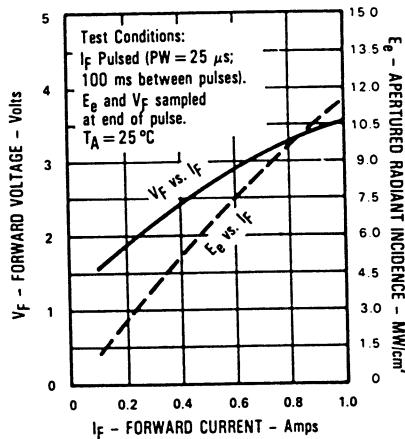
INFRARED
EMITTING
DIODES

Typical Performance Curves

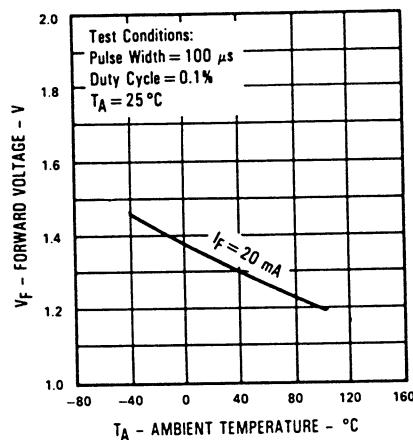
Forward Voltage vs
Forward Current



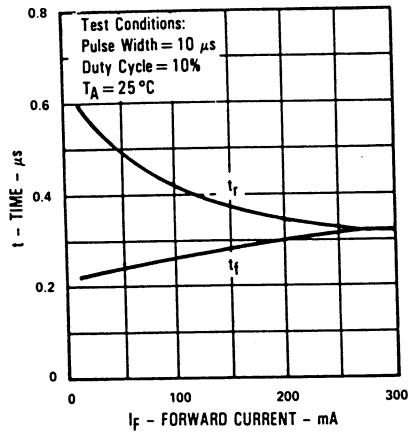
Forward Voltage and Radiant Incidence
vs Forward Current



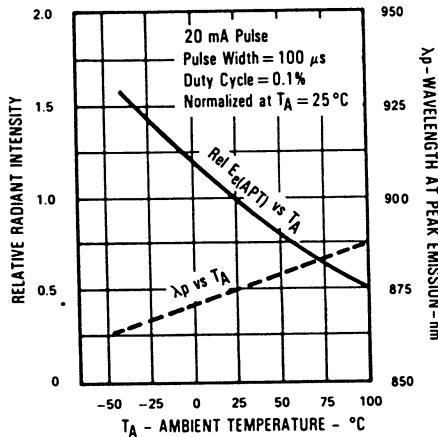
Forward Voltage vs
Ambient Temperature



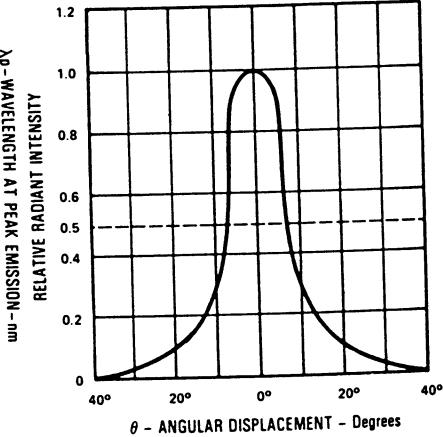
Rise Time and Fall Time vs
Forward Current



Relative Radiant Intensity and Wavelength
at Peak Emission vs Ambient Temperature



Relative Radiant Intensity vs
Angular Displacement



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Optek Technology, Inc.

1215 W. Crosby Road

Carrollton, Texas 75006

(972)323-2200

Fax (972)323-2396